



Docket No.: 061352-0041

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
Hiroyuki FURUYA, et al.	:	Confirmation Number: 2093
Application No.: 10/620,432	:	Group Art Unit: 2812
Filed: July 17, 2003	:	Examiner: MULPURI, SAVITRI

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR  
SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED  
SEMICONDUCTOR DEVICE

**RESPONSE TO COMMUNICATION DATED JUNE 21, 2005**

**Attn: Decisions and Certificate of Correction Branch**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**Certificate  
AUG 08 2005  
of Correction**

Sir:

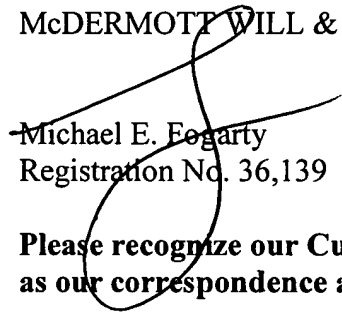
In response to your communication dated June 21, 2005, denying the request for correction of the error under Foreign Patent Documents, we respectfully request reconsideration of the Certificate of Correction regarding insertion of – KR 2010583 A-- on the title page of Letters Patent US 6,806,109 under "FOREIGN PATENT DOCUMENTS" for the following reason (Photocopy of the Certificate of Correction request filed on May 26, 2005 is attached). Contrary to the conclusion reached in denying the previous request for the Certificate of Correction, the reference in question has been previously considered during prosecution as is made clear by the Examiner's initials placed next the reference on the PTO-1449 form signed by the Examiner and returned to the Applicants. A photocopy of this

PTO-1449 form initialed by the examiner and returned to us on May 6, 2004 as part of the Notice of Allowance is attached. As is clear, the PTO-1449 form shows the initials of the examiner reflecting that the reference KR 2010583 was considered.

In light of this evidence we ask that a Certificate of Correction be issued reflecting the Korean Reference –KR 2010583 A --.

Respectfully submitted,

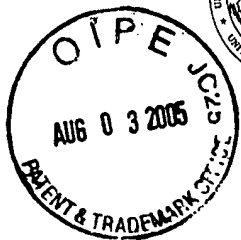
McDERMOTT WILL & EMERY LLP

  
~~Michael E. Fogarty~~  
Registration No. 36,139

**Please recognize our Customer No. 20277  
as our correspondence address.**

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
Phone: 202.756.8000 MEF:jgh  
Facsimile: 202.756.8087  
**Date: August 3, 2005**

AUG 09 2005

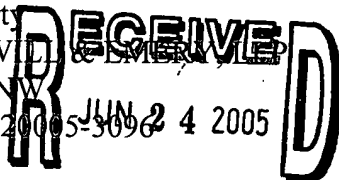


UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents  
United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450  
[www.uspto.gov](http://www.uspto.gov)

Date : June 21, 2005

Michael E. Fogarty  
McDERMOTT WILL & EMERY LLP  
600 13<sup>TH</sup> Street, NW  
Washington, DC 20005-3096



MW&E

**Patent No:** 6806109 B2

**Applicant:** Hiroyuki Furuya, et al.

**Issued:** October 19, 2004

**Title:** METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD  
OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

**Request for Certificate of Correction:**

Consideration had been given to your request for the issuance of a certificate of correction for the above-identified patent under the provisions of Rule 1.322.

Respecting the alleged error under Foreign Patent Documents, the patent is printer in accordance with the record, since the references was not in conformance and not considered. Therefore, no correction is in order here under 1.322 or 1.323.

In view of the foregoing, your request in this matter is hereby **denied**.

**A certificate of correction will be issued to correct the remaining error mentioned in your request.**

Correspondence concerning this matter should be filed and directed to Decisions and Certificate of Correction Branch.

Virginia Tolbert  
For Cecelia Newman, Supervisor  
Decisions and Certificate of Correction  
(703) 305-8309 or 308-9390 ext. 113

vt

AUG 09 2005



SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.  
61352-041SERIAL NO.  
10/620,432APPLICANT  
Hiroyuki FURUYA, et al.FILING DATE  
July 17, 2003GROUP  
2812

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
Su		JP 2001-176813 A (w/ English Abstract) ✓	06/29/2001	NICHIA CHEM. IND., LTD.			
		JP 2001-342100 A (w/ partial English translation) ✓	12/11/2001	TOSHIBA CORP.			
		EP 1 278 233 A1 (WO 01/084608) ✓	01/22/2003	TOYODA GOSHI CO., LTD.			
		JP 2001-168042 A (w/ English Abstract)(WO 00/55893) ✓	06/22/2001	mitsubishi cable ind., LTD.			
		EP 1 184 897 A1 ✓	03/06/2000	mitsubishi cable ind., LTD.			
		JP 2001-93837 A (w/ English Abstract) ✓	04/06/2001	CANON INC.			
		J 2002-353152 A (w/ English Abstract) ✓	12/06/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2002-110569 A (w/ English Abstract) ✓	04/12/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2000-228539 A (w/ English Abstract) ✓	08/15/2000	SHARP CORP.			
		JP 11-191657 (w/ English Abstract) ✓	07/13/1999	NICHIA CHEM. IND., LTD.			
		JP 2001-313259 A ✓		Copy not enclosed.			
		AU 3607601 A ✓		Copy not enclosed.			
		JP 2000-156002 A ✓		Copy not enclosed.			
		JP 2000-331947 A ✓		Copy not enclosed.			
		JP 2000-331937 A ✓		Copy not enclosed.			
		KR 2010583 A ✓		Copy not enclosed.			

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
Su		I. KIDOGUCHI et al., "Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth", Jpn. J. Appl. Phys., Part 2, Vol. 39, No. 5B, (2000), pages L453-456.
Su		S. NAKAMURA, "InGaN/GaN/A1GaN-based laser diodes grown on epitaxially laterally overgrown GaN", Journal of Materials Research, Commentaries and Reviews, Vol. 14, No. 7, July 1999, pages 2716-2731.
Su		S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN/GaN/A1GaN-Based Laser Diodes Grown on Pure GaN Substrates", Jpn. J. Appl. Phys., Vol. 37, 15 March 1998, pages L309-L312.

EXAMINER

DATE CONSIDERED

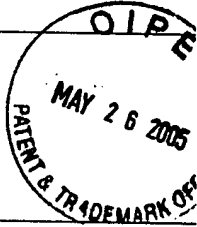
3/9/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.



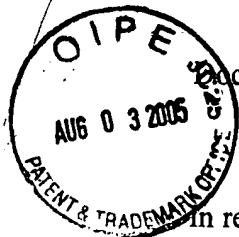
Applicant: Hiroyuki FURUYA, et al. Docket No. 061352-0041 Serial No. 10/620,4  
Title: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE Patent No. 6,806,10  
Date Sent: 5/26/2005 ☒ Hand Carried ☐ Fax ☐ Electronic ☐ Cert. of Mailing ☐ First Class Mail ☐ Express Mail No.  
☐ Transmittal Letter  
New Patent App ☐ Utility ☐ Design ☐ Cont. ☐ CIP ☐ Div. ☐ PCT ☐ RCE ☐ Prov  
☐ Other: \_\_\_\_\_  
\_\_\_\_\_ pages of Specification  
\_\_\_\_\_ pages of Claims  
\_\_\_\_\_ pages of Abstract  
\_\_\_\_\_ pages of Formal/Informal Drawings  
☐ Small Entity ☒ Large Entity  
☐ Declaration/Power of Attorney  
☐ Recordation of Assignment/Security Agreement  
☐ Information Disclosure Statement  
\_\_\_\_\_ Form PTO 1449  
\_\_\_\_\_ copies of cited references  
☐ Preliminary Amendment  
☐ Response to Missing Parts Notice  
☐ Resp. to Notice to Correct App. Papers  
☐ Certified Copy of Priority Doc.  
☐ Claim for Convention Priority  
☐ Response/Amendment to Office Action of  
☐ Request for \_\_\_\_\_ month Extension of Time  
☐ Letter submitting \_\_\_\_\_ pages of drawings  
☐ Req. for Approval of Drawing Amendments  
☐ Req. for Oral Hearing  
☐ Not. of Appeal ☐ Appeal Brief ☐ Reply Brief  
☐ Rule 312 Amendment/Letter  
☐ Req. for Acknowledgement of Cited Art  
☐ Issue Fee  
☐ Publication Fee  
☒ Req. for Certificate of Correction  
☐ Maintenance Fee for \_\_\_\_\_ years after grant  
☐ Fee Address Indication Form  
☐ Terminal Disclaimer  
☐ Petition to Commissioner  
☐ Status Inquiry  
☒ Other Form 1050



Check for	\$	<input type="checkbox"/> Charge Deposit Acct. 500417	\$	Atty Init.	MEF	Tkpr. #	3328	Secy. or PL:	BDeHart
-----------	----	--	----	------------	-----	---------	------	--------------	---------

CMS Descrip.: \_\_\_\_\_

THE PATENT AND TRADEMARK OFFICE DATE STAMPED HEREON IS ACKNOWLEDGEMENT THAT THE ITEMS, CHECKED ABOVE, WERE RECEIVED BY THE PTO ON THE DATE STAMPED



Docket No.: 061352-0041

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Hiroyuki FURUYA, et al.

Application No.: 10/620,432  
Patent No. 6,806,109 B2

Filed: July 17, 2003

Issued: October 19, 2004

Customer Number: 20277

Confirmation Number: 2093

Group Art Unit: 2812

Examiner: MULPURI, SAVITRI

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE  
AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

**REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322**

Mail Stop Box 4/ Certificates of Correction  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In reviewing the above-identified patent, a printing error was discovered therein requiring correction in order to conform the Official Record in the application.

The error noted is set forth on the attached copy of form PTO-1050 Rev. 2-93 in the manner required by the Commissioner's Notice.

Specifically, on the title page, side 1, Item "(56)", under "FOREIGN PATENT DOCUMENTS", the Korean reference --KR 2010583 A -- should be inserted. In addition, on side 2 of the title page, at the bottom of the listed "U.S. PATENT DOCUMENTS", the following U.S. Published application data should be inserted -- 2003/0203629 10/2005 Ishibashi et al .....438/689 --. Copies of the initialed PTO-1449 form listing the Korean application and PTO-892 listing the published application are attached for your information and convenience.

**AUG 09 2005**

**10/620,432**

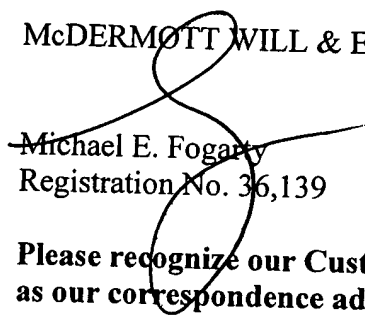
Patent No. 6,806,109 B2

The change requested herein occurred as a result of printing the Letters Patent and the Certificate should be issued without expense under Rule 322 of the Rules of Practice. Accordingly, Applicants request issuance of the Certificate of Correction.

Please charge any shortage in fees due in connection with the filing of this paper to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP

  
~~Michael E. Fogarty~~  
Registration No. 36,139

**Please recognize our Customer No. 20277  
as our correspondence address.**

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
Phone: 202.756.8000 MEF:BD  
Facsimile: 202.756.8087  
**Date: May 26, 2005**

WDC99 1087520-1.061352.0041

**AUG 09 2005**

aplo  
are  
nly!

PRINTER'S TRIM LINE

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,806,109 B2

DATED : October 19, 2004

INVENTOR(S): Hiroyuki FURUYA, et al.

It is certified that error appears in the above-identified patent and that said Letter Patent is hereby corrected as shown below:

ON THE TITLE PAGE, side 1,

Item ("56"), under "FOREIGN PATENT DOCUMENTS", insert the following:

-- KR 2010583 A -- ;

ON THE TITLE PAGE, side 2,

Below the listed "U.S. PATENT DOCUMENTS", insert

-- 2003/0203629 10/2005 Ishibashi et al .....438/689 -- .

AUG 09 2005